

Triacs

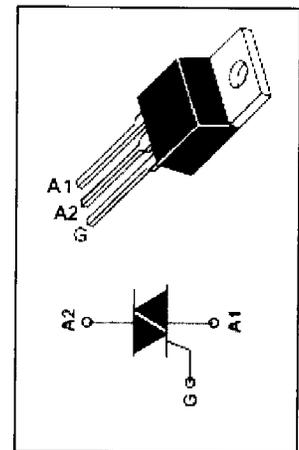
TIC226M

FEATURES

- With TO-220 package
- Sensitive Gate Triacs
- Glass Passivated
- Max I_{GT} of 50 mA (Quadrants 1~3)

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak reverse voltage	600	V
$I_{T(RMS)}$	RMS on-state current (full sine wave) $T_C=85^\circ\text{C}$	8	A
I_{TSM}	Non-repetitive peak on-state current	70	A
T_j	Operating junction temperature	110	$^\circ\text{C}$
T_{stg}	Storage temperature	-45~150	$^\circ\text{C}$
$R_{th(j-c)}$	Thermal resistance, junction to case	1.8	$^\circ\text{C/W}$
$R_{th(j-a)}$	Thermal resistance, junction to ambient	62.5	$^\circ\text{C/W}$



ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX	UNIT	
I_{DRM}	Repetitive peak off-state current	$V_D=V_{DRM}$, $T_c=110^\circ\text{C}$		2.0	mA	
I_{GT}	Gate trigger current	$V_{supply} = 12\text{V}\uparrow$; $R_L = 10\ \Omega$; $t_{p(g)} > 20\ \mu\text{s}$	I	2	50	mA
			II	12	50	
			III	9	50	
			IV	20		
I_H	Holding current	$V_{supply} = 12\text{V}\uparrow$; $I_G = 0$ initial $I_{TM}=100\text{mA}$		30	mA	
V_{GT}	Gate trigger voltage all quadrant	$V_{supply} = 12\text{V}\uparrow$; $R_L = 10\ \Omega$; $t_{p(g)} > 20\ \mu\text{s}$		2	V	
V_{TM}	On-state voltage	$I_T = 12\text{A}$; $I_G = 50\text{mA}$		2.1	V	

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